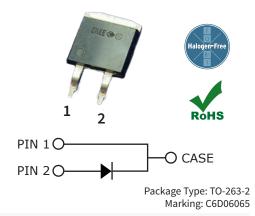
6th Generation 650 V, 6 A Silicon Carbide Schottky Diode

Description

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.



Features

- Low Forward Voltage (V_F) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior
- Low Leakage Current (I_p)

Applications

- Industrial Power Supplies
- Switch Mode Power Supplies
- Server / Telecom Power Supplies
- Power Factor Correction
- Solar Inverter
- Uninterruptible Power Supply

Maximum Ratings $(T_c = 25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Value	Unit	Test Conditions	Note	
Repetitive Peak Reverse Voltage	V_{RRM}	650	- V			
DC Blocking Voltage	V _{DC}	650				
Continuous Forward Current	I _F	23	- - - - A	T _J = 25 °C		
		12		T _J = 125 °C	Fig. 3	
		6		T _J = 155 °C		
Repetitive Peak Forward Surge Current	I _{FRM}	25		$T_c = 25 ^{\circ}\text{C}$, $t_p = 10 \text{ms}$, Half Sine Wave		
		14		$T_c = 110 ^{\circ}\text{C}$, $t_p = 10 \text{ms}$, Half Sine Wave		
Non-Repetitive Peak Forward Surge Current	l _{FSM} -	45		$T_c = 25 ^{\circ}\text{C}$, $t_p = 10 \text{ms}$, Half Sine Wave	Fig. 8	
		33		$T_c = 110 ^{\circ}\text{C}$, $t_p = 10 \text{ms}$, Half Sine Wave		
	I _{F, Max} -	620	_	$T_c = 25 ^{\circ}\text{C}$, $t_p = 10 \mu\text{s}$, Pulse		
		570	-	$T_c = 110 {}^{\circ}\text{C}, t_p = 10 \mu\text{s}, \text{Pulse}$		
	P _{tot} -	73	- W	T _J = 25 °C	— Fig. 4	
Power Dissipation		31		T ₁ = 110 °C		

Electrical Characteristics

Parameter	Symbol	Тур.	Max.	Units	Test Conditions	Note	
Drain-Source Voltage	V	1.27	1.40	— v	I _F = 6 A, T _J = 25 °C	- Fig. 1	
	$V_{_{\rm F}}$	1.37	1.50		I _F = 6 A, T _J = 175 °C		
Reverse Current	I _R	2	20		V _R = 650 V, T _J = 25 °C	- Fig. 2	
		25	200	— μΑ	V _R = 650 V, T _J = 175 °C		
Total Capacitive Charge	Q _c	22		nC	V _R = 400 V, T _J = 25 °C	Fig. 5	
		393			$V_R = 0 \text{ V}, T_J = 25 \text{ °C}, f = 1 \text{ MHz}$		
Total Capacitance	С	44		— pF	V _R = 200 V, T _J = 25 °C, f = 1 MHz	Fig. 6	
		36			$V_R = 400 \text{ V}, T_J = 25 \text{ °C}, f = 1 \text{ MHz}$		
Capacitance Stored Energy	E _c	3.5		μJ	V _R = 400 V	Fig. 7	

Note:

 $\label{thm:continuous} \mbox{SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.}$

Thermal & Mechanical Characteristics

Parameter	Symbol	Тур.	Units	Note	
Thermal Resistance, Junction to Case	$R_{\theta, JC}$	2.05	°C/W		
Operating Junction & Storage Temperature	$T_{_{\!J}},T_{_{\!stg}}$	-55 to +175	°C	Fig. 9	

Typical Performance

Figure 1. Forward Characteristics

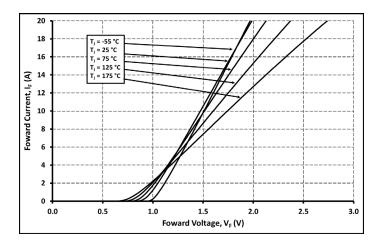


Figure 3. Current Derating

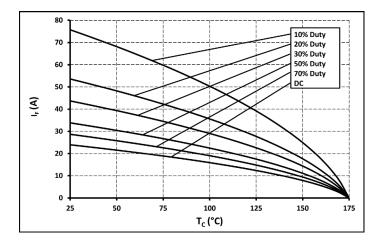


Figure 5. Total Capacitance Charge vs. Reverse

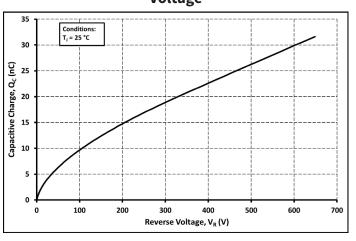


Figure 2. Reverse Characteristics

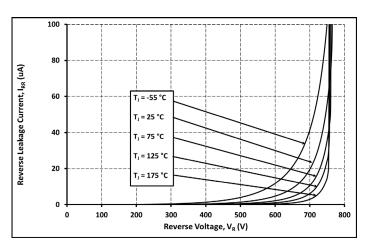


Figure 4. Power Derating

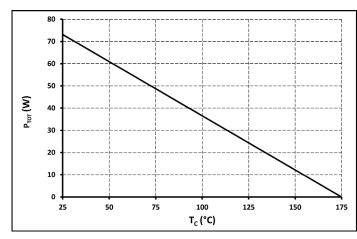
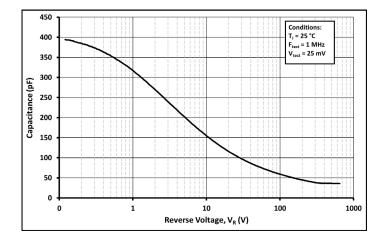


Figure 6. Capacitance vs. Reverse Voltage



4

Typical Performance

Figure 7. Capacitance Stored Energy

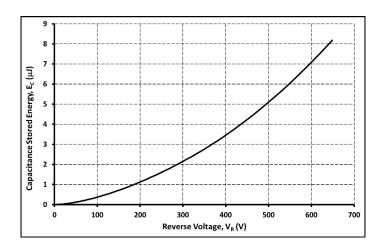


Figure 8. Non-Repetitive Peak Forward Surge Current (Sine Wave)

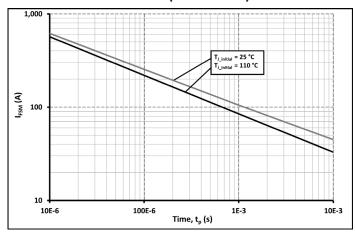
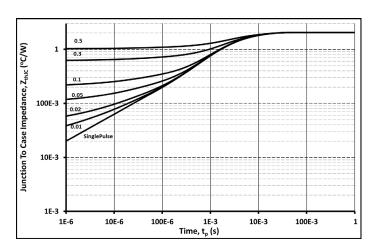


Figure 9. Transient Thermal Impedance

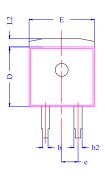


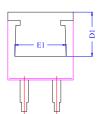
Electrostatic Discharge (ESD) Classifications

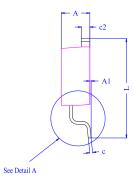
Parameter	Symbol	Class
Human Body Model	НВМ	Class 3B (≥ 8000 V)
Charge Device Model	CDM	Class C3 (≥ 1000 V)

Package Dimensions

Package: TO-263-2 All dimensions in mm.



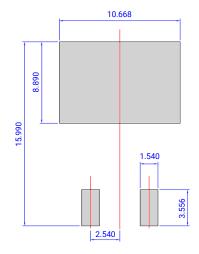






Dim	Min	Тур	Max		
A	4.32	4.445	4.57		
A1		0.20	0.25		
b	0.71	0.825	0.94		
b2	1.15	1.275	1.4		
c	0.356	0.4955	0.635		
c2	1.22	1.31	1.4		
D	8.89	9.145	9.4		
D1	6.48	6.78	6.88		
Е	10.04	10.16	10.28		
E1	7.535	7.980	8.425		
e	2.54				
L	14.73	15.24	15.75		
L1	2.29	2.54	2.79		
L2	1.15	1.27	1.39		
θ	0°	4°	8°		

Recommended Solder Pad Layout



Learn more about recommended soldering profiles in this application note.

Notes

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